2SD669(A)

Rev.F Mar.-2016

蓝箭电子 BLUE ROCKET ELECTRONICS

DATA SHEET

/ Descriptions

WR0459I ṂṂ Ł QSQ ÆṀ ч s ‖ ㄱ Silicon NPN transistor in a TO-126F Plastic Package.

/ Features

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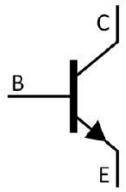
Complementary pair with 2SB649(A).

/ Applications

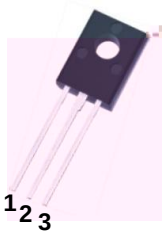
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Low frequency power amplifier.

/ Equivalent Circuit



/ Pinning



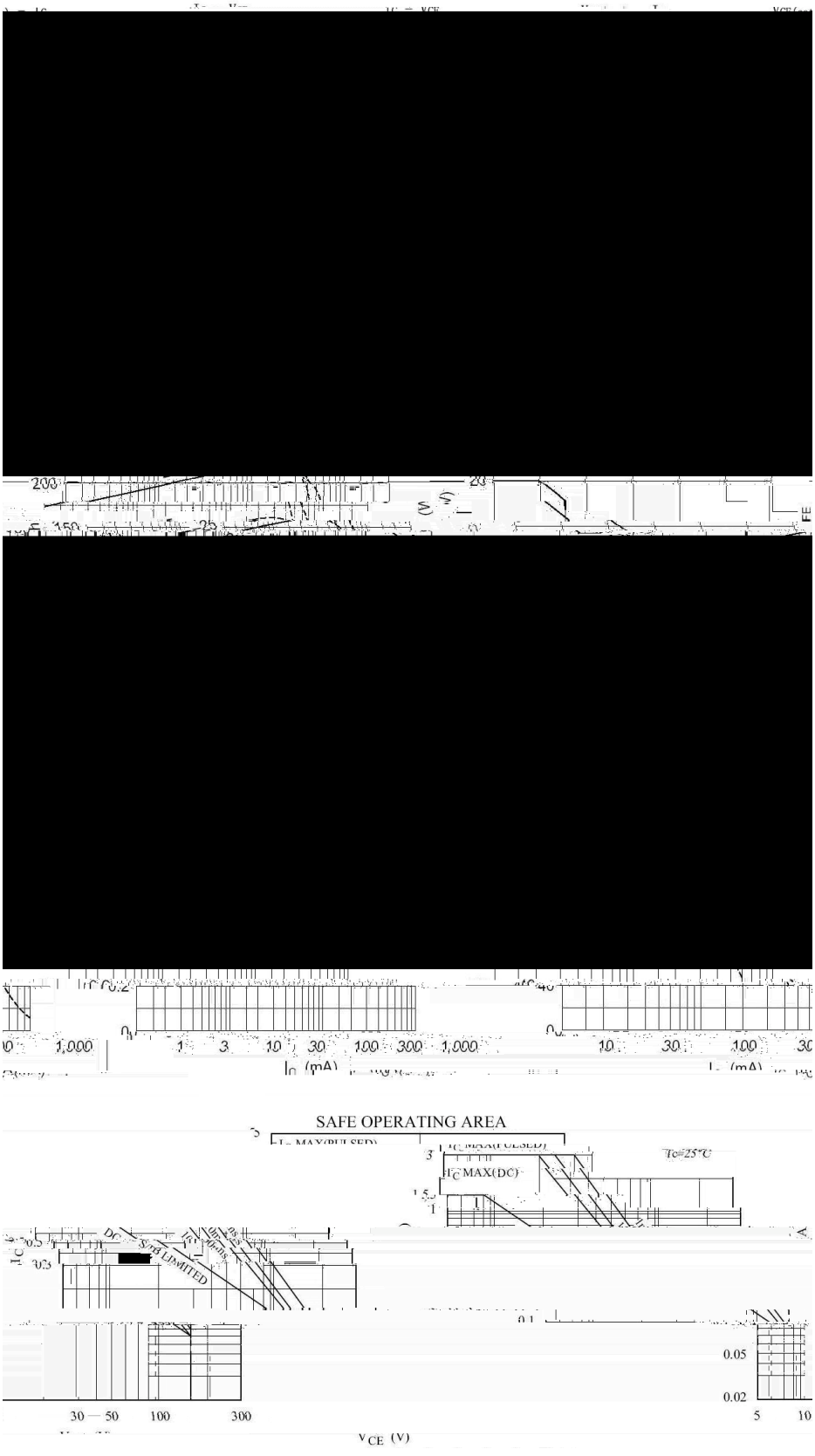
PIN1 χ Emitter PIN 2 χ Collector PIN 3 χ Base

/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	B	C	D
h_{FE} Range	60 120	100 200	160 320

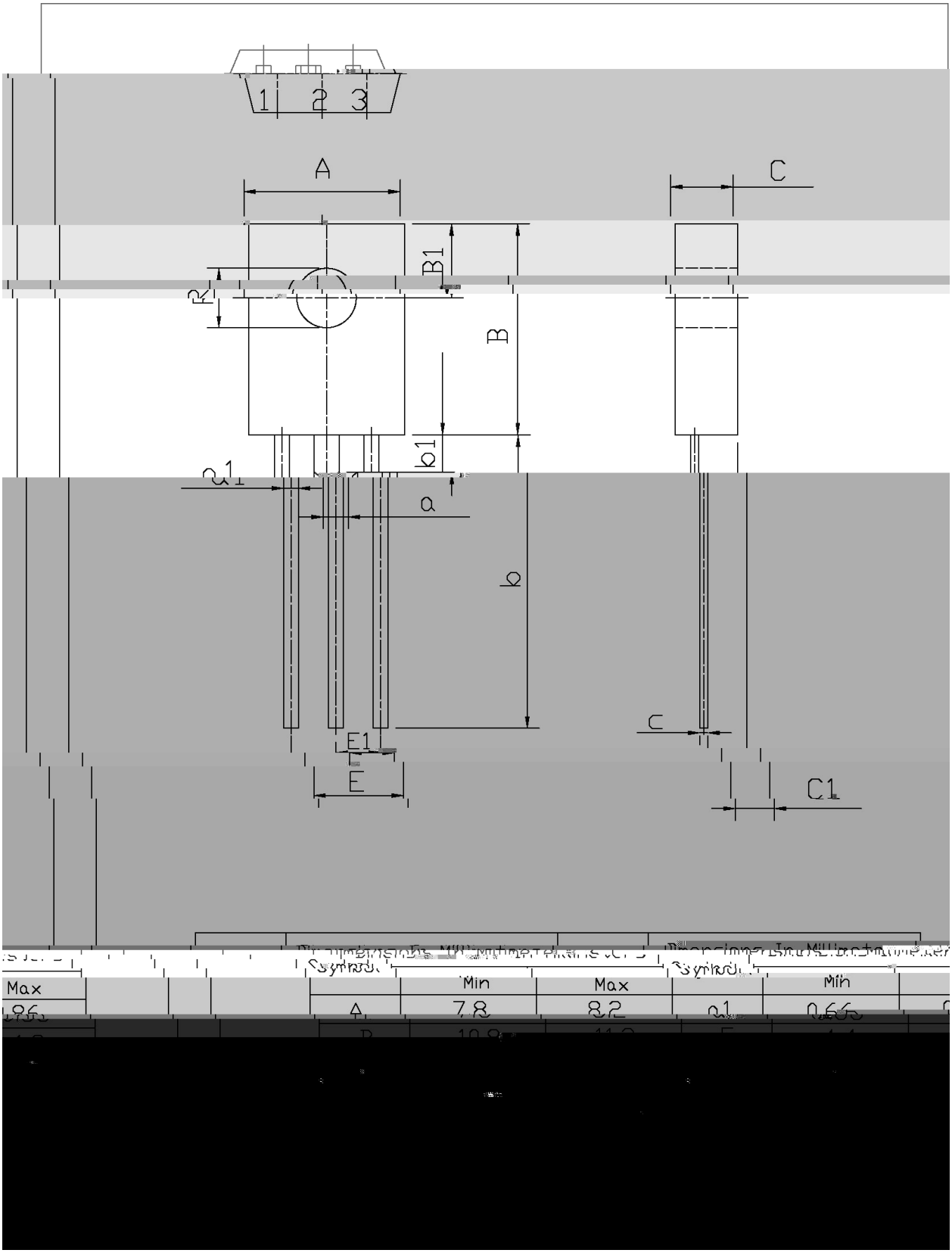
v ¨Ω Parameter	ϒ N Symbol		¨Ω Ö Rating	D Ђ Unit
Collector to Base Voltage	V_{CBO}		180	V
Collector to Emitter Voltage	V	2SD669	120	

/ Electrical Characteristic Curve



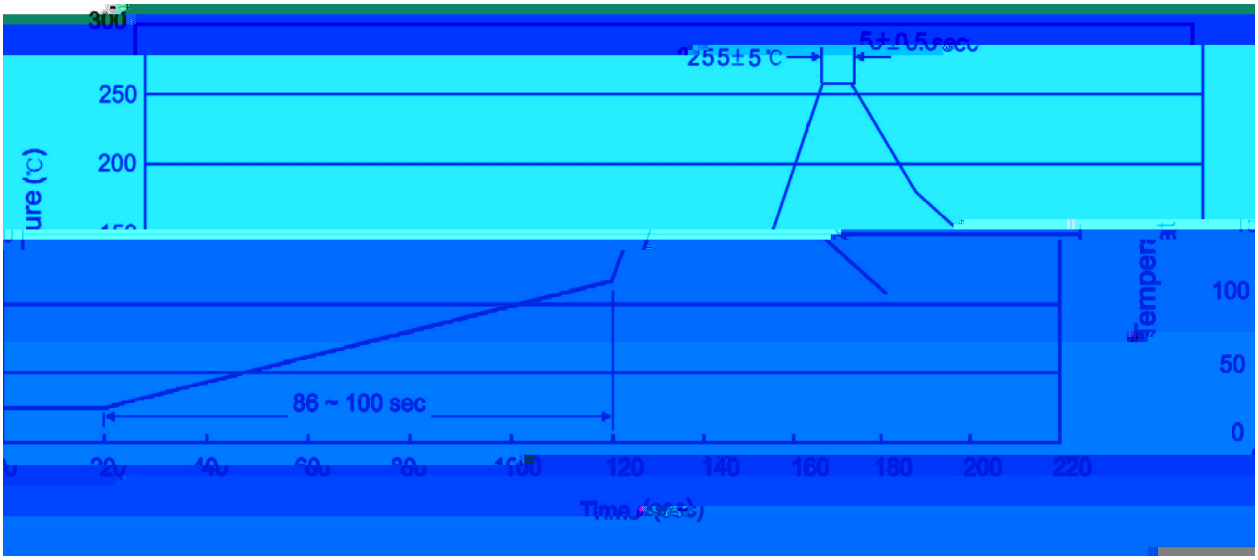
/ Package Dimensions

TO-126T 单位：mm



Symbol	Min	Max	Symbol	Min	Max
A	7.8	8.2	a1	0.65	

( ) / Temperature Profile for Dip Soldering(Pb-Free)



ب ˝ χ

1 Ĺ ♬ □ ỷ 25 Ḱ 150 ł ı ˋH ڑ 60 Ḱ 90sec;

2 Š Ө □ ỷ 255 ° 5 ł ı ˋH ڑ ˋY ﾊ ㎛ 5 ° 0.5sec;

3 ì ˙ ﾘ ˛ ɔ ﻉ ỷ ㎛ 2 Ḱ 10 ł /sec.

Note:

1.Preheating:25~150 ł , Time:60~90sec.

2.Peak Temp.:255 ° 5 ł , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ł /sec.

5 • **ƕ** **q** **ł** ˜ 255 °